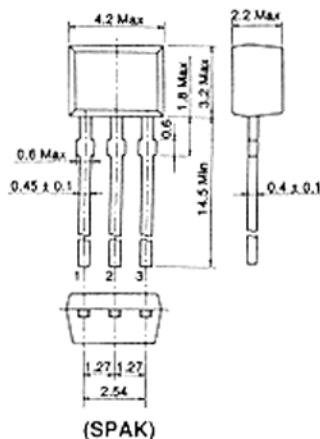


2SC3836

SILICON NPN EPITAXIAL

LOW FREQUENCY AMPLIFIER · SWITCHING

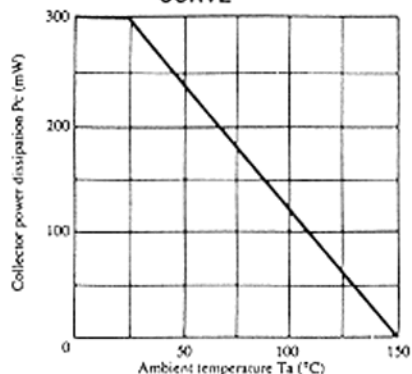


1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC3836	Unit
Collector to base voltage	V _{CB0}	60	V
Collector to emitter voltage	V _{CE0}	50	V
Emitter to base voltage	V _{EB0}	15	V
Collector current	I _C	300	mA
Collector power dissipation	P _C	300	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE

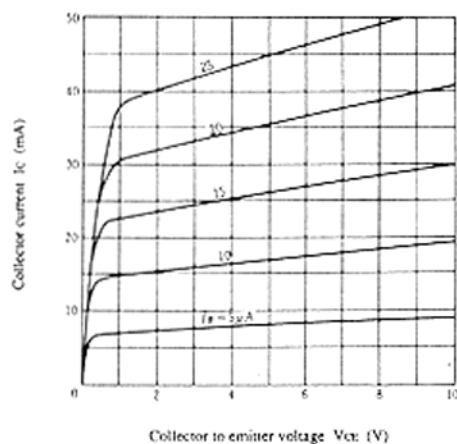


■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

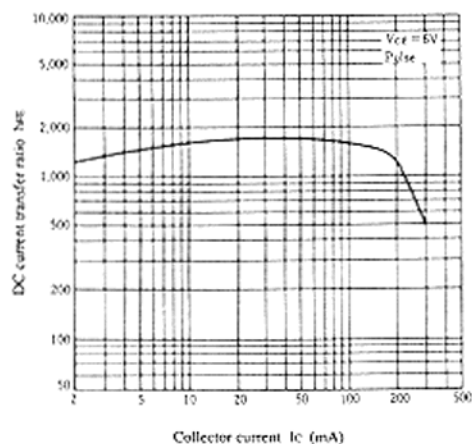
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	60	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	50	—	—	V
Emitter to base breakdown voltage	V _{(BE)EBO}	I _E = 10μA, I _C = 0	15	—	—	V
Collector cutoff current	I _{CB0}	V _{CE} = 50V, I _E = 0	—	—	1	μA
Base to emitter voltage	V _{BE}	V _{CE} = 6V, I _C = 1mA	—	—	0.75	V
DC current transfer ratio	h _{FE1}	V _{CE} = 6V, I _C = 100mA (pulse test)	800	—	2000	
	h _{FE2}	V _{CE} = 6V, I _C = 1mA	500	—	—	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 300mA, I _B = 30mA (pulse test)	—	—	0.3	V

2SC3836

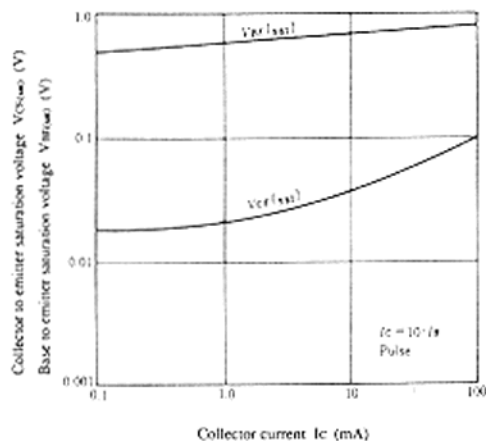
TYPICAL OUTPUT CHARACTERISTICS



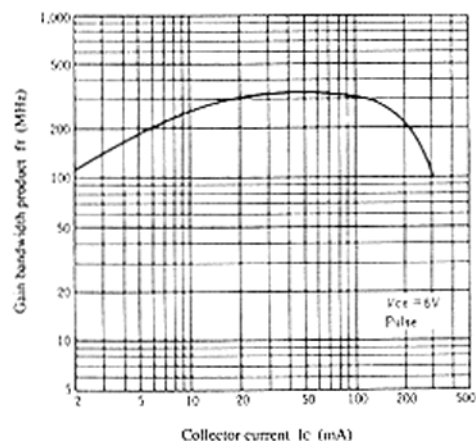
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE

